

POWER MOSFET CATALOG



Wayon Electronics Co., Ltd.

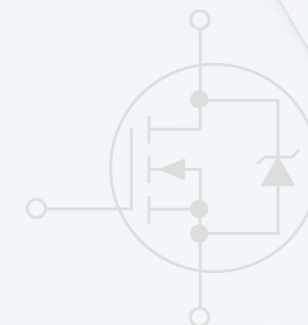
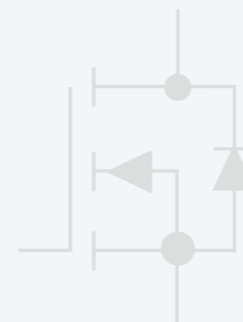
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WAYON掌握深沟槽和多次外延超结MOSFET技术, 拥有全面的产品矩阵, 超结MOSFET产品规格覆盖500V-1200V, 2A-99A。WAYON国内首家量产耐压1000V以上的超结MOSFET, 推出国内超低导通电阻的600V/16.5mΩ产品, 并推出创新的内置绝缘、SOT-223-2L、PDFN8X8等封装产品。

WAYON masters both Deep trench and Multi-EPI super junction MOSFET technology, and has very comprehensive products portfolio. Super junction MOSFET product specifications cover 500V-1200V, 2A-99A. WAYON is the first domestic mass-produced super-junction MOSFET with a withstand voltage of over 1000V, and possess 600V/16.5mΩ products as ultra-low Rdson, and introduced innovative built-in insulation package, SOT-223-2L, PDFN8X8 and other package products.

WAYON坚持客户为中心、以市场为导向的理念, 强调高品质和领先技术竞争力, 已成为三星、LG、富士康、中兴、华为、Amazon、OSRAM、光宝、赛尔康、长虹、海信、小米、全汉、长城、核达中远通、茂硕、崧盛、Vivo、康舒、立讯精密、和硕、雷士等国内外知名企业供应商。

WAYON adheres to the customer-centric and market-oriented concept, and emphasizes high quality and leading technological competitiveness. It has become the supplier of Samsung, LG, Foxconn, ZTE, Huawei, Amazon, OSRAM, Lite-On, SALCOMP, CHANGHONG, Hisense, Xiaomi, FSP, GreatWall, VAPEL, MOSO, SOSEN, Vivo, ACBEL, LUXSHARE, PEGATRON, NVC and other well-known domestic and foreign enterprises.



上海维安(WAYON)成立于1996年, 总部位于上海浦东新区, 专注于功率半导体及电路保护产品的研发, 是全球少数几家掌握先进电路保护及功率半导体核心技术的供应商。主要产品包括功率半导体产品、电路保护产品和混合信号类IC产品。

Wayon Electronics (WAYON) was established in 1996 and is headquartered in Shanghai Pudong New Area. It focuses on the research and development of power semiconductors and circuit protection products. It is one of the few suppliers in the world that masters advanced circuit protection and power semiconductor core technologies. The main products include power semiconductor products, circuit protection products and mixed-signal IC etc.





Wayon WMOS™ 3rd Generation Technology

C4 Series Power MOSFET

The very high power density super junction technology

Introduction

Based on very high power density super junction technology Wayon WMOS™ C4 will improve the switching related Figures of Merit(FOM) and application performance characteristics substantially. This technology achieves up to 30% better FOM ($R_{DS(on)} * Q_g$) versus the previous WMOS™ C2 technology and is cost-effective.

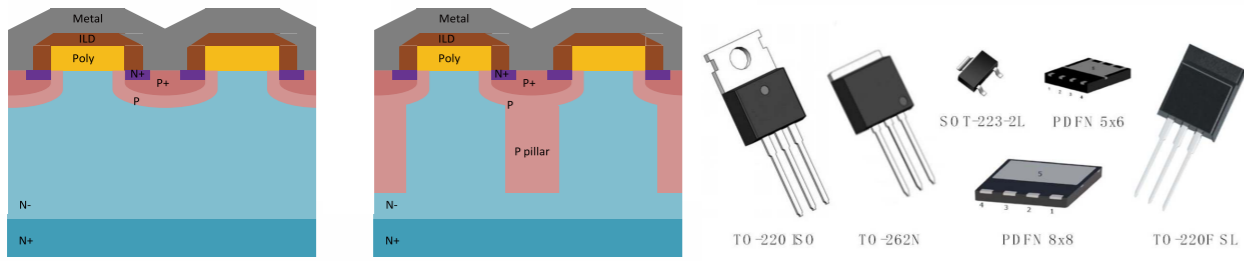


Figure 1 Device structure: SJ-MOS VS VDMOS

Key Features & Benefits

- Superior EMI and Surge ability
- Ultra low $R_{DS(on)}$ resulting in low conduction losses and improved efficiency in end-applications
- Ultra low gate charge that improves switching performance
- 100% avalanche tested
- Voltage range: 500V-1200V
- Advanced packaging technology
- Green package

Main Applications

- Charger
- Adapter
- PC
- TV
- LED/Lighting
- UPS/Server
- EV Charger
- Industrial Power Supply

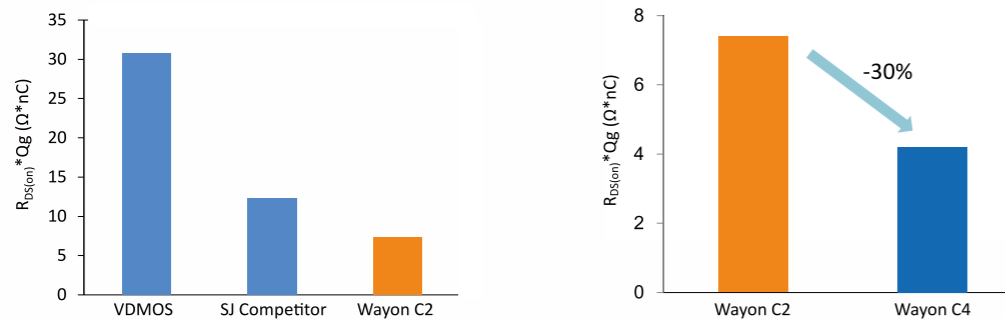
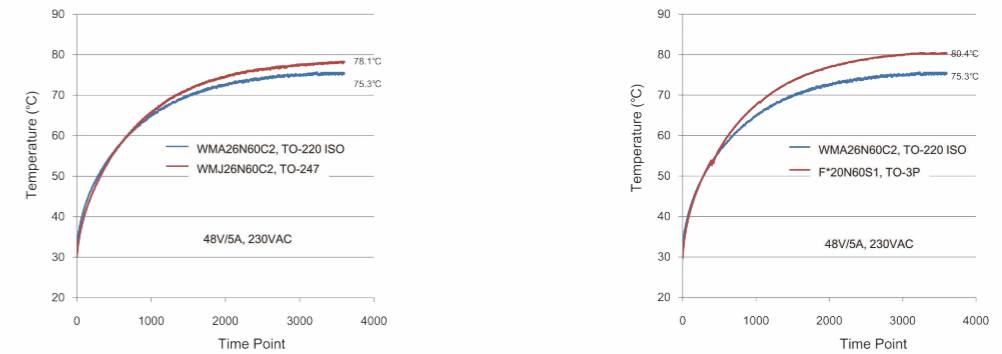


Figure 2. FOM Comparison

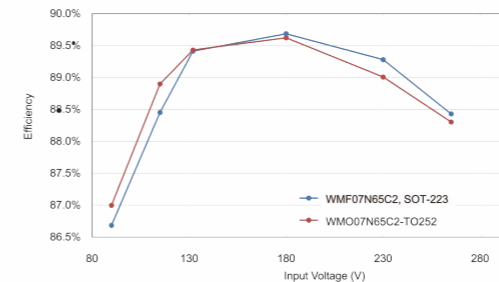
Application case:240W LED

Temperature Comparison: (Innovative Package TO-220 ISO vs. TO-247 and TO-3P, Temp. 25°C)

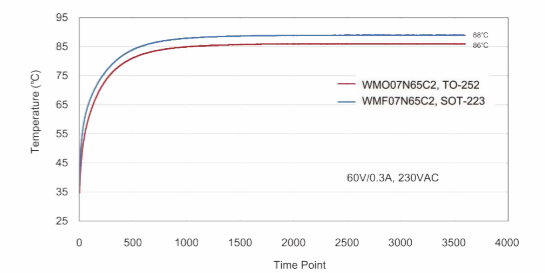


Application case : 18W charger

Efficiency Comparison (SOT-223-2L vs. TO-252)



Temperature Comparison (SOT-223-2L vs. TO-252)



Application case

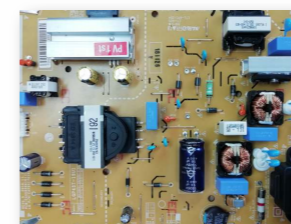
Korean Customer * 25W 5G Cellpone fast charging



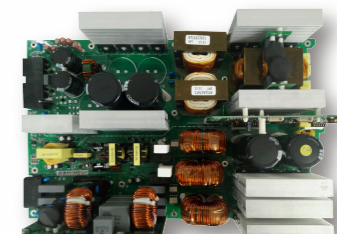
Customer * 2000W Server Power supply



Korean Customer * 120W TV Power Supply



Customer* EV-Charger





SJ-MOS SR Product Portfolio

650V SJ-MOSFET SR

$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
0.6	WMO11N65SR	WMP11N65SR	WML11N65SR	WMK11N65SR	WMM11N65SR	WMN11N65SR	
0.38	WMO14N65SR	WMP14N65SR	WML14N65SR	WMK14N65SR	WMM14N65SR	WMN14N65SR	
0.35	WMO16N65SR	WMP16N65SR	WML16N65SR	WMK16N65SR	WMM16N65SR	WMN16N65SR	
0.198			WML26N65SR	WMK26N65SR	WMM26N65SR	WMN26N65SR	WMJ26N65SR
0.04							WMJ80N65SR*
0.03							WMJ90N65SR

700V SJ-MOSFET SR

$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
0.61	WMO11N70SR	WMP11N70SR	WML11N70SR	WMK11N70SR	WMM11N70SR	WMN11N70SR	
0.395	WMO14N70SR	WMP14N70SR	WML14N70SR	WMK14N70SR	WMM14N70SR	WMN14N70SR	
0.36	WMO16N70SR	WMP16N70SR	WML16N70SR	WMK16N70SR	WMM16N70SR	WMN16N70SR	
0.21			WML26N70SR	WMK26N70SR	WMM26N70SR	WMN26N70SR	WMJ26N70SR

SJ-MOS C4 Product Portfolio

500V SJ-MOSFET C4

$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
0.95	WMO06N50C4	WMP06N50C4*	WML06N50C4	WMK06N50C4*	WMM06N50C4*	WMN06N50C4*	
0.65	WMO10N50C4	WMP10N50C4*	WML10N50C4	WMK10N50C4*	WMM10N50C4*	WMN10N50C4*	
0.48	WMO13N50C4	WMP13N50C4	WML13N50C4	WMK13N50C4	WMM13N50C4	WMN13N50C4	
0.3	WMO18N50C4	WMP18N50C4	WML18N50C4	WMK18N50C4	WMM18N50C4	WMN18N50C4	
0.27	WMO22N50C4	WMP22N50C4	WML22N50C4	WMK22N50C4	WMM22N50C4	WMN22N50C4	
0.16	WMO25N50C4	WMP25N50C4	WML25N50C4	WMK25N50C4	WMM25N50C4	WMN25N50C4	WMJ25N50C4
0.125			WML28N50C4	WMK28N50C4	WMM28N50C4	WMN28N50C4	WMJ28N50C4
0.085			WML40N50C4	WMK40N50C4	WMM40N50C4	WMN40N50C4	WMJ40N50C4

600V SJ-MOSFET C4

$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.14	WMO07N60C4	WMP07N60C4	WML07N60C4	WMK07N60C4	WMM07N60C4	WMN07N60C4	
0.78	WMO08N60C4	WMP08N60C4	WML08N60C4	WMK08N60C4	WMM08N60C4	WMN08N60C4	
0.6	WMO10N60C4	WMP10N60C4	WML10N60C4	WMK10N60C4	WMM10N60C4	WMN10N60C4	
0.38	WMO14N60C4	WMP14N60C4	WML14N60C4	WMK14N60C4	WMM14N60C4	WMN14N60C4	
0.3	WMO15N60C4	WMP15N60C4	WML15N60C4	WMK15N60C4	WMM15N60C4	WMN15N60C4	
0.19	WMO26N60C4	WMP26N60C4	WML26N60C4	WMK26N60C4	WMM26N60C4	WMN26N60C4	
0.16			WML28N60C4	WMK28N60C4	WMM28N60C4	WMN28N60C4	WMJ28N60C4
0.097			WML36N60C4	WMK36N60C4	WMM36N60C4	WMN36N60C4	WMJ36N60C4
0.07			WML53N60C4		WMM53N60C4	WMN53N60C4	WMJ53N60C4
0.039							WMJ80N60C4
0.029							WMJ90N60C4
0.023							WMJ99N60C4
0.0185							WMJ120N60C4

650V SJ-MOSFET C4

$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.14	WMO07N65C4	WMP07N65C4	WML07N65C4	WMK07N65C4	WMM07N65C4	WMN07N65C4	
0.78	WMO08N65C4	WMP08N65C4	WML08N65C4	WMK08N65C4	WMM08N65C4	WMN08N65C4	
0.6	WMO10N65C4	WMP10N65C4	WML10N65C4	WMK10N65C4	WMM10N65C4	WMN10N65C4	
0.38	WMO14N65C4	WMP14N65C4	WML14N65C4	WMK14N65C4	WMM14N65C4	WMN14N65C4	
0.3	WMO15N65C4	WMP15N65C4	WML15N65C4	WMK15N65C4	WMM15N65C4	WMN15N65C4	
0.19	WMO26N65C4	WMP26N65C4	WML26N65C4	WMK26N65C4	WMM26N65C4	WMN26N65C4	
0.16			WML28N65C4	WMK28N65C4	WMM28N65C4	WMN28N65C4	WMJ28N65C4
0.097			WML36N65C4	WMK36N65C4	WMM36N65C4	WMN36N65C4	WMJ36N65C4
0.07			WML53N65C4		WMM53N65C4	WMN53N65C4	WMJ53N65C4
0.039							WMJ80N65C4
0.029							WMJ90N65C4
0.023							WMJ99N65C4



700V SJ-MOSFET C4							
$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.14	WMO07N70C4	WMP07N70C4*	WML07N70C4	WMK07N70C4*	WMM07N70C4*	WMN07N70C4*	
0.78	WMO08N70C4	WMP08N70C4*	WML08N70C4	WMK08N70C4*	WMM08N70C4*	WMN08N70C4*	
0.6	WMO10N70C4	WMP10N70C4*	WML10N70C4	WMK10N70C4*	WMM10N70C4*	WMN10N70C4*	
0.38	WMO14N70C4	WMP14N70C4*	WML14N70C4	WMK14N70C4*	WMM14N70C4*	WMN14N70C4*	
0.3	WMO15N70C4	WMP15N70C4*	WML15N70C4	WMK15N70C4*	WMM15N70C4*	WMN15N70C4*	

SJ-MOS EM Product Portfolio

700V SJ-MOSFET EM & MM							
$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.5	WMO05N70MM	WMP05N70MM	WML05N70MM	WMK05N70MM	WMM05N70MM	WMN05N70MM	
1.3	WMO06N70EM*	WMP06N70EM*	WML06N70EM*	WMK06N70EM*	WMM06N70EM*	WMN06N70EM*	
0.95	WMO08N70EM*	WMP08N70EM*	WML08N70EM*	WMK08N70EM*	WMM08N70EM*	WMN08N70EM*	
0.6	WMO10N70EM	WMP10N70EM	WML10N70EM	WMK10N70EM	WMM10N70EM	WMN10N70EM	
0.39	WMO13N70EM	WMP13N70EM	WML13N70EM	WMK13N70EM	WMM13N70EM	WMN13N70EM	
0.28	WMO18N70EM	WMP18N70EM	WML18N70EM	WMK18N70EM	WMM18N70EM	WMN18N70EM	WMJ18N70EM
0.25	WMO20N70EM	WMP20N70EM	WML20N70EM	WMK20N70EM	WMM20N70EM	WMN20N70EM	WMJ20N70EM
0.2			WML25N70EM	WMK25N70EM	WMM25N70EM	WMN25N70EM	WMJ25N70EM
0.16			WML30N70EM	WMK30N70EM	WMM30N70EM	WMN30N70EM	WMJ30N70EM

650V SJ-MOSFET EM & MM							
$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.5	WMO05N65MM	WMP05N65MM	WML05N65MM	WMK05N65MM	WMM05N65MM	WMN05N65MM	
1.2	WMO06N65EM*	WMP06N65EM*	WML06N65EM*	WMK06N65EM*	WMM06N65EM*	WMN06N65EM*	
0.95	WMO08N65EM	WMP08N65EM*	WML08N65EM*	WMK08N65EM*	WMM08N65EM*	WMN08N65EM*	
0.6	WMO10N65EM	WMP10N65EM	WML10N65EM	WMK10N65EM	WMM10N65EM	WMN10N65EM	
0.39	WMO13N65EM	WMP13N65EM	WML13N65EM	WMK13N65EM	WMM13N65EM	WMN13N65EM	
0.28	WMO18N65EM	WMP18N65EM	WML18N65EM	WMK18N65EM	WMM18N65EM	WMN18N65EM	WMJ18N65EM
0.24	WMO20N65EM	WMP20N65EM	WML20N65EM	WMK20N65EM	WMM20N65EM	WMN20N65EM	WMJ20N65EM
0.19			WML25N65EM	WMK25N65EM	WMM25N65EM	WMN25N65EM	WMJ25N65EM
0.16			WML30N65EM	WMK30N65EM	WMM30N65EM	WMN30N65EM	WMJ30N65EM
0.06							WMJ60N65EM
0.043							WMJ80N65EM

SJ-MOS with Fast Body Diode(F2 Series)

600V SJ-MOSFET F2							
$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
0.68	WMO10N60F2	WMP10N60F2	WML10N60F2	WMK10N60F2	WMM10N60F2	WMN10N60F2	
0.43	WMO14N60F2	WMP14N60F2	WML14N60F2	WMK14N60F2	WMM14N60F2	WMN14N60F2	
0.34	WMO15N60F2	WMP15N60F2	WML15N60F2	WMK15N60F2	WMM15N60F2	WMN15N60F2	
0.22	WMO26N60F2	WMP26N60F2	WML26N60F2	WMK26N60F2	WMM26N60F2	WMN26N60F2	
0.19			WML28N60F2	WMK28N60F2	WMM28N60F2	WMN28N60F2	WMJ28N60F2
0.11			WML36N60F2	WMK36N60F2	WMM36N60F2	WMN36N60F2	WMJ36N60F2
0.078			WML53N60F2				WMJ53N60F2
0.044							WMJ80N60F2
0.033							WMJ90N60F2
0.025							WMJ99N60F2

650V SJ-MOSFET F2							
$R_{DS(on)}$, max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
0.68	WMO10N65F2	WMP10N65F2	WML10N65F2	WMK10N65F2	WMM10N65F2	WMN10N65F2	
0.43	WMO14N65F2	WMP14N65F2	WML14N65F2	WMK14N65F2	WMM14N65F2	WMN14N65F2	
0.34	WMO15N65F2	WMP15N65F2	WML15N65F2	WMK15N65F2	WMM15N65F2	WMN15N65F2	
0.22	WMO26N65F2	WMP26N65F2	WML26N65F2	WMK26N65F2	WMM26N65F2	WMN26N65F2	
0.19			WML28N65F2	WMK28N65F2	WMM28N65F2	WMN28N65F2	WMJ28N65F2
0.11			WML36N65F2	WMK36N65F2	WMM36N65F2	WMN36N65F2	WMJ36N65F2
0.078			WML53N65F2				WMJ53N65F2
0.044							WMJ80N65F2
0.031							WMJ90N65F2



SOT223-2L 封装					
R _{DS(on)} max[Ω]	600V	650V	700V	800V	900V
2.5					WMF06N90C2
2.1				WMF06N80M3	
2.0	WMF04N60C2	WMF04N65C2			
1.6		WMF05N65MM	WMF05N70MM		
1.2	WMF07N60C4	WMF07N65C4			
0.80	WMF08N60C4	WMF08N65C4			
0.61	WMF10N60C4	WMF10N65C4			

PDFN5*6 封装		
R _{DS(on)} max[Ω]	600V	650V
0.40		WMB13N65EM
0.39	WMB14N60C4	WMB14N60C4
0.30		WMB18N65EM

PDFN8*8 封装			
R _{DS(on)} max[Ω]	600V	650V	700V
0.39	WMZ14N60C4	WMZ13N65EM	
0.25			WMZ20N70EM
0.2	WMZ26N60C4	WMZ26N65C4	
0.2	WMZ28N60F2		
0.102	WMZ36N60C4	WMZ36N65C4	
0.072	WMZ53N60C4	WMZ53N65C4	
0.079	WMZ53N60F2	WMZ53N65F2	

内置绝缘封装					
Package	R _{DS(on)} max[Ω]	600V	650V	700V	800V
TO-220 ISO	0.405	WMA14N60C2*	WMA14N65C2*		WMA25N80M3
	0.32	WMA16N60C2*	WMA16N65C2*		
	0.19	WMA26N60C2	WMA26N65C2		
TO-3P ISO	0.075	WMC53N60F2			

维安实验室 Wayon lab

器件与应用测试能力

Device and application testing capabilities

- 器件测试(无损) Device testing (non-destructive)
- 雷击浪涌测试 Surge testing
- 抗扰度测试 EFT testing
- 静电测试 ESD testing
- 雪崩测试 EAS testing

失效分析能力

Failure analysis capability

- DECAP、取DIE、弹坑实验 Crater test
- 无损X-RAY观察能力 Non-destructive X-RAY observation
- 器件级及裸芯片切片实验 Device level & die slice test
- 器件级及芯片级的电性测试 Device level & die electrical test

可靠性试验能力

Reliability test capability

气候环境试验

Environment test

- 高温贮存试验 (HTSL)
- 稳态湿热试验 (THT)
- 低温贮存试验 (LTSL)
- 高压蒸煮试验 (AC/PCT)
- 温度冲击试验 (TST)
- 高速老化寿命试验 (UFAST)

负载老化试验

Aging test

- 高温反偏 (HTRB, HTGB)
- 高温高湿偏置试验 (H3TRB)
- 高速老化寿命试验 (HAST)
- 间歇寿命试验 (IOL)

编号 NO.	设备名称 Equipment	型号 PN	试用测试项目 Test item
1	分立器件功率老化系统 Discrete device power aging system	BTD-E810	IOL
2	高加速老化试验箱 Highly accelerated aging test chamber	PC-422R8	UFAST/HAST
3	高温反偏实验系统 High temperature reverse bias experimental system	BTR-E600	HTRB/HTGB/HTSL
4	高温反偏试验系统 High temperature reverse bias test system	BTR-E600D	HTRB/HTGB/HTSL
5	三端稳压器高温老化系统 Three-terminal regulator high temperature aging system	BTD-E852	HTOL
6	冷热冲击试验箱 Thermal shock test chamber	ES-76EX	TST
7	恒温恒湿箱 Constant temperature and humidity chamber	SETH-Z-021L	Pre-conditioning/THT/H3TRB
8	恒温恒湿箱 Constant temperature and humidity chamber	H/HWHS-150L	Pre-conditioning/THT/H3TRB
9	饱和高压加速老化试验机 Saturated high pressure accelerated aging test machine	R-PCT-350	AC
10	高低温试验箱 Temperature chamber	H/GDW-100L	HTSL/LTSL



SJ-MOS M3 product portfolio

800V SJ-MOSFET M3

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
4.0	WMO03N80M3	WMP03N80M3	WML03N80M3	WMK03N80M3	WMM03N80M3	WMN03N80M3	
2.3	WMO05N80M3	WMP05N80M3	WML05N80M3	WMK05N80M3	WMM05N80M3	WMN05N80M3	
2.0	WMO06N80M3	WMP06N80M3	WML06N80M3	WMK06N80M3	WMM06N80M3	WMN06N80M3	
1.8	WMO07N80M3	WMP07N80M3	WML07N80M3	WMK07N80M3	WMM07N80M3	WMN07N80M3	
1.38	WMO08N80M3	WMP08N80M3	WML08N80M3	WMK08N80M3	WMM08N80M3	WMN08N80M3	
1.03	WMO10N80M3	WMP10N80M3	WML10N80M3	WMK10N80M3	WMM10N80M3	WMN10N80M3	
0.8	WMO11N80M3	WMP11N80M3	WML11N80M3	WMK11N80M3	WMM11N80M3	WMN11N80M3	
0.62	WMO12N80M3	WMP12N80M3	WML12N80M3	WMK12N80M3	WMM12N80M3	WMN12N80M3	WMJ12N80M3
0.48	WMO13N80M3	WMP13N80M3	WML13N80M3	WMK13N80M3	WMM13N80M3	WMN13N80M3	WMJ13N80M3
0.36			WML15N80M3	WMK15N80M3	WMM15N80M3	WMN15N80M3	WMJ15N80M3
0.26			WML25N80M3	WMK25N80M3	WMM25N80M3	WMN25N80M3	WMJ25N80M3
0.195			WML30N80M3	WMK30N80M3	WMM30N80M3	WMN30N80M3	WMJ30N80M3
0.128			WML35N80M3				WMJ35N80M3
0.075							WMJ65N80M3*

800V SJ-MOSFET S

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.5	WMO80R1K0S	WMP80R1K0S	WML80R1K0S	WMK80R1K0S	WMM80R1K0S	WMN80R1K0S	
1.1	WMO80R850S	WMP80R850S	WML80R850S	WMK80R850S	WMM80R850S	WMN80R850S	
0.83	WMO80R720S	WMP80R720S	WML80R720S	WMK80R720S	WMM80R720S	WMN80R720S	
0.5	WMO80R600S	WMP80R600S	WML80R600S	WMK80R600S	WMM80R600S	WMN80R600S	
0.36	WMO80R350S	WMP80R350S	WML80R350S	WMK80R350S	WMM80R350S	WMN80R350S	WMJ80R350S
0.26	WMO80R260S	WMP80R260S	WML80R260S	WMK80R260S	WMM80R260S	WMN80R260S	WMJ80R260S

900V SJ-MOSFET C2

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
5.2	WMO03N90C2	WMP03N90C2	WML03N90C2	WMK03N90C2	WMM03N90C2	WMN03N90C2	
3.1	WMO05N90C2	WMP05N90C2	WML05N90C2	WMK05N90C2	WMM05N90C2	WMN05N90C2	
2.5	WMO06N90C2	WMP06N90C2	WML06N90C2	WMK06N90C2	WMM06N90C2	WMN06N90C2	
2.0	WMO07N90C2	WMP07N90C2	WML07N90C2	WMK07N90C2	WMM07N90C2	WMN07N90C2	
1.37	WMO09N90C2	WMP09N90C2	WML09N90C2	WMK09N90C2	WMM09N90C2	WMN09N90C2	

900V SJ-MOSFET S

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
1.5	WMO90R1K5S	WMP90R1K5S	WML90R1K5S	WMK90R1K5S	WMM90R1K5S	WMN90R1K5S	
1.1	WMO90R1K1S	WMP90R1K1S	WML90R1K1S	WMK90R1K1S	WMM90R1K1S	WMN90R1K1S	
0.83	WMO90R830S	WMP90R830S	WML90R830S	WMK90R830S	WMM90R830S	WMN90R830S	
0.5	WMO90R500S	WMP90R500S	WML90R500S	WMK90R500S	WMM90R500S	WMN90R500S	WMJ90R500S
0.36	WMO90R360S	WMP90R360S	WML90R360S	WMK90R360S	WMM90R360S	WMN90R360S	WMJ90R360S
0.26	WMO90R260S	WMP90R260S	WML90R260S	WMK90R260S	WMM90R260S	WMN90R260S	WMJ90R260S

950V SJ-MOSFET C2

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
2.7	WMO05N95C2	WMP05N95C2	WML05N95C2	WMK05N95C2	WMM05N95C2	WMN05N95C2	WMJ12N95C2
1.85	WMO07N95C2	WMP07N95C2	WML07N95C2	WMK07N95C2	WMM07N95C2	WMN07N95C2	WMJ15N95C2
1.1	WMO08N95C2	WMP08N95C2	WML08N95C2	WMK08N95C2	WMM08N95C2	WMN08N95C2	
0.86	WMO11N95C2	WMP11N95C2	WML11N95C2	WMK11N95C2	WMM11N95C2	WMN11N95C2	
0.55			WML12N95C2	WMK12N95C2	WMM12N95C2	WMN12N95C2	
0.44			WML15N95C2	WMK15N95C2	WMM15N95C2	WMN15N95C2	

1000V SJ-MOSFET C2

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
3.5	WMO05N100C2	WMP05N100C2	WML05N100C2	WMK05N100C2	WMM05N100C2	WMN05N100C2	
2.5	WMO07N100C2	WMP07N100C2	WML07N100C2	WMK07N100C2	WMM07N100C2	WMN07N100C2	
1.4	WMO10N100C2	WMP10N100C2	WML10N100C2	WMK10N100C2	WMM10N100C2	WMN10N100C2	
0.8			WML12N100C2	WMK12N100C2	WMM12N100C2	WMN12N100C2	WMJ12N100C2

1050V SJ-MOSFET C2

$R_{DS(on)}$ max[Ω]	TO-252	TO-251	TO-220F	TO-220	TO-263	TO-262	TO-247
3.5	WMO05N105C2	WMP05N105C2	WML05N105C2	WMK05N105C2	WMM05N105C2	WMN05N105C2	
2.5	WMO07N105C2	WMP07N105C2	WML07N105C2	WMK07N105C2	WMM07N105C2	WMN07N105C2	
1.4	WMO10N105C2	WMP10N105C2	WML10N105C2	WMK10N105C2	WMM10N105C2	WMN10N105C2	
0.8			WML12N105C2	WMK12N105C2	WMM12N105C2	WMN12N105C2	WMJ12N105C2



参考设计 Reference design

基于平板变压器和超结SJ-MOSFET的高功率密度电源设计

Design of high power density power supply based on flat transformer and SJ-MOSFET

规格 spec

Input voltage: 90-264Vac

Input current : <1.5A

Frequency: 47-67Hz

Output voltage & current: 5V3A&9V3A&15V3A*20V3.25A

OCP: $\geq 105\% \cdot I_o$

Output voltage ripple : <200 mV(线端测试 Wire end test , 并联10uF电容, 带宽20MHz)

Average efficiency meet: COC V5 Tier2 energy efficiency requirements

Start delay time : <2s

Dynamic overshoot/back hook : <5%*Vo (10%-90%负载, 5ms/5ms, 0.8A/us)

MOSFET:

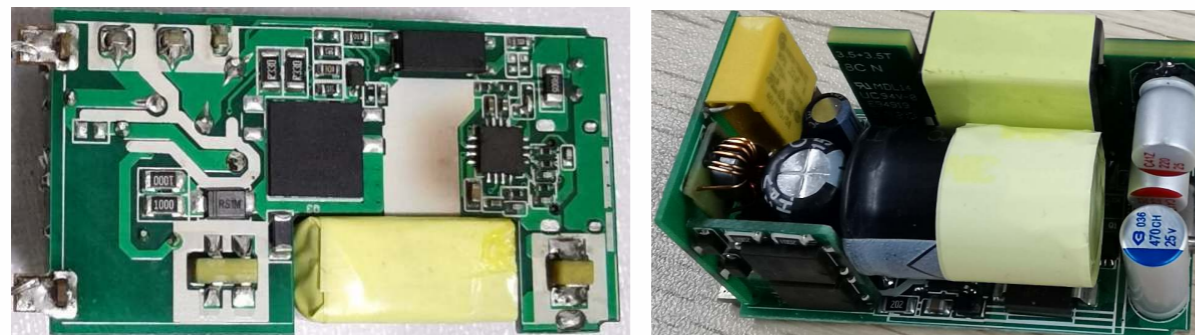
WMZ26N60C4, WMB060N10LG2, WMQ40N03T1

可以提供完整的PCBA, BOM, 原理图和测试报告

Can share complete PCBA, BOM, schematic diagram and test report

PCBA尺寸长*宽*高:

49.5mm* 27mm*25.4mm



NOTE.